SUB C2

35. Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

an inner conductive core spaced from and suspended over the outer surface;

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a polymer dielectric layer surrounding a substantial portion of the inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer.

36. Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;

an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;

a polymer dielectric layer over a substantial portion of the inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer.

37. Integrated circuitry comprising:

a substrate having an outer surface;

a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;

a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;

a conductive layer of material disposed over and operably connected with the copper-comprising layer of material, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt, and iron;

a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding conductive layer portions which extend between the terminal members; and

an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members.

38. The integrated circuitry of claim 35, wherein the outer conductive sheath leaves some void space between the outer conductive sheath and the outer surface.

39. The integrated circuitry of claim 35, wherein the outer conductive sheath is not formed on the outer surface.

40. The integrated circuitry of claim 35, wherein the polymer dielectric layer comprises parylene.

41. The integrated circuitry of claim 35, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

42. The integrated circuitry of claim 35, wherein the outer conductive sheath comprises aluminum.

43. The integrated circuitry of claim 35, wherein the inner conductive core comprises copper.

44. The integrated circuitry of claim 35, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

45. The integrated circuitry of claim 36, wherein the polymer dielectric layer comprises parylene.

46. The integrated circuitry of claim 36, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

47. The integrated circuitry of claim 36, wherein the outer conductive sheath comprises aluminum.

48. The integrated circuitry of claim 36, wherein the inner conductive core comprises copper.

49. The integrated circuitry of claim 36, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

50. Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

an inner conductive core spaced from and over the outer surface;

a polymer dielectric layer surrounding a substantial portion of the suspended inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed on the outer surface.

SUB C3

51. The integrated circuitry of claim 50, wherein the polymer dielectric layer comprises parylene.

52. The integrated circuitry of claim 50, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

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53. The integrated circuitry of claim 50, wherein the outer conductive sheath comprises aluminum.

54. The integrated circuitry of claim 50, wherein the inner conductive core comprises copper.

55. The integrated circuitry of claim 50, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

56. Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;

an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;

a polymer dielectric layer surrounding the suspended inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer while some void space is present between the dielectric layer over the suspended inner conductive core and the outer surface, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed over the substrate outer surface.

57. The integrated circuitry of claim 56, wherein the polymer dielectric layer comprises parylene.

58. The integrated circuitry of claim 56, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

59. The integrated circuitry of claim 56, wherein the outer conductive sheath comprises aluminum.

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60. The integrated circuitry of claim 56, wherein the inner conductive core comprises copper.

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61. The integrated circuitry of claim 56, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

62. Integrated circuitry comprising:

a substrate having an outer surface;

a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;

a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;

a conductive layer of material operably connected with the copper-comprising layer of material and suspended above the outer surface between the terminal members, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt, and iron;

a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding the suspended conductive layer portions; and

an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed over the substrate outer surface.